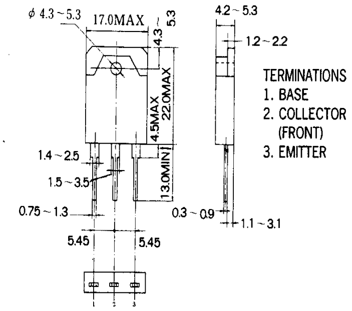
2SD1063 NPN PLANAR SILICON TRANSISTOR

- **PSW / D / DDC**
- **COMPLEMENTARY TO 2SB827**

SC-65



ABSOLUTE MAXIMUM RATING (T_A=25℃)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base voltage	V_{EBO}	6	V
Collector Current (DC)	I_C	7	A
Collector Dissipation	P_C	60	W
Junction Temperature	T_j	150	℃
Storage Temperature	Tstg	-55~150	℃

ELECTRICAL CHARACTERISTICS (T_A=25℃)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Collector Base Breakdown Voltage	BV_{CBO}	I_C=5 mA I_E=0	60			V
Collector Emitter Breakdown Voltage	BV_{CEO}	I_C=10 mA R_{BE}=∞	50			V
Emitter Base Breakdown Voltage	BV_{EBO}	I_E=5mA I_C=0	6			V
Collector Cutoff Current	I_{CBO}	V_{CB}=60V I_E=0			0.1	mA
Emitter Cutoff Current	I_{EBO}	V_{EB}=4V I_C=0			0.1	mA
*DC Current Gain	H_{fe}	V_{CE}=2V I_C=1A	70		280	
Collector- Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=4A I_B=0.4A			0.4	V